

Case N . 62603



**DIRECTOR, U.S. PATENT AND TRADEMARK OFFICE
WASHINGTON, DC 20231**

In re Application of: **MEARS**

Serial No.: **10/647,061**

Filed: **AUGUST 22, 2003**

For: **METHOD FOR MAKING SEMICONDUCTOR DEVICE
INCLUDING BAND-ENGINEERED SUPERLATTICE**

Sir:

Transmitted herewith is an INFORMATION DISCLOSURE STATEMENT in the above-identified application.

1. This IDS is submitted under 37 C.F.R. § 1.97. No fee is required.
2. This IDS is submitted under 37 C.F.R. § 1.97(c). Enclosed is a check in the amount of \$180.00.
3. This IDS is submitted under 37 C.F.R. § 1.97(c) and (e). No fee is required.
4. This IDS is submitted under 37 C.F.R. § 1.97(d) and (e). Enclosed is a check in the amount of \$130.00 to cover the petition fee.
5. The Commissioner is hereby authorized to charge or credit any discrepancies in fee amounts to Deposit Account No. 01-0484.
6. Please associate this application with Customer No. 27975.

 **27975**

PATENT TRADEMARK OFFICE

Date: October 2, 2003


CHRISTOPHER F. REGAN
Reg. No. 34,906



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:)
MEARS)
Serial No. 10/647,061)
Filing Date: AUGUST 22, 2003)
For: METHOD FOR MAKING SEMICONDUCTOR))
DEVICE INCLUDING BAND-)
ENGINEERED SUPERLATTICE)

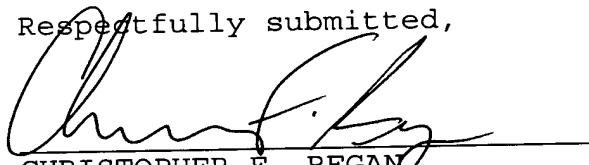
CITATION UNDER 37 CFR §1.97

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Attached is Form PTO-1449 listing several references for consideration in the examination of the above-identified application. A copy of each reference is also enclosed. It is requested that these references be considered by the Examiner and officially made of record in accordance with the provisions of 37 CFR §1.97 and Section 609 of the MPEP.

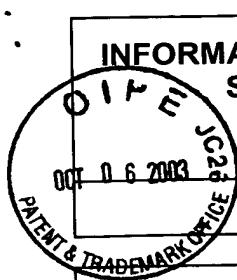
Respectfully submitted,


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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: COMMISSIONER FOR PATENTS, P.O. BOX 1450, ALEXANDRIA, VA 22313-1450, on this 2nd day of October, 2003.




**INFORMATION DISCLOSURE
STATEMENT**

Atty Docket:
Serial No.:
Applicant:
Filing Date:
Group:
62603
10/647,061
MEARS
AUGUST 22, 2003

U.S. PATENT DOCUMENTS

Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
	AA	4,594,603	06/10/86	Holonyak, Jr.	357	16	01/24/85
	AB	4,937,204	06/26/90	Ishibashi et al.	437	110	01/4/89
	AC	4,969,031	11/06/90	Kobayashi et al.	357	63	02/3/83
	AD	5,05,887	10/08/91	Yamazaki	357	4	01/18/90
	AE	5,216,262	06/1/93	Tsu	257	17	03/2/92
	AF	5,357,119	10/18/94	Wang et al.	257	18	02/19/93
	AG	5,684,817	11/04/97	Houdre et al.	372	45	05/1/96
	AH	5,683,934	11/4/03	Candelaria	437	134	05/3/96
	AI	5,994,164	11/30/99	Fonash et al.	438	97	03/18/98
	AJ	6,058,127	05/2/00	Joannopoulos et al.	372	92	12/12/97
	AK	6,274,007	08/14/01	Smirnov et al.	204	192	03/14/00
	AL	6,281,518	08/28/01	Sato	257	13	12/3/98
	AM	6,281,532	08/28/01	Doyle et al.	257	288	06/28/99
	AN	6,344,271	02/05/02	Yadav et al.	428	402	03/23/99
	AO	6,472,685	10/29/02	Takagi	257	77	12/2/98
	AP	6,498,359	12/24/02	Schmidt et al.	257	190	05/18/01
	AQ	2003/ 0034529	02/20/03	Fitzgerald et al.	257	369	10/8/02
	AR	2003/ 0057416	03/27/03	Currie et al.	257	19	09/20/02

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub Class	Translation
	AS	02/103767	12/27/02	WO	H01L	21/20	
	AT	2,347,520	09/06/00	GB	G02B	5/18	
	AU						

EXAMINER:**DATE CONSIDERED:**

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;
Draw line through citation if not in conformance and not considered. Include copy of this form with next
communication to applicant.



INFORMATION DISCLOSURE STATEMENT		Atty Docket: Serial No.: Applicant: Filing Date: Group:
		62603 10/647,061 MEARS AUGUST 22, 2003

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)		
	AV	Xuan Luo et al.; "Chemical Design of Direct-Gap Light-Emitting Silicon", published July 25, 2002 by The American Physical Society; Vol. 89, Number 7
	AW	R. Tsu; University of North Carolina at Charlotte, "Phenomena in Silicon Nanostructure Devices"; published 09/06/2000 © Springer-Verlag 2000
	AX	P.D. Ye et al., "GaAs MOSFET with Oxide Gate Dielectric Grown by Atomic Layer Deposition"; © 2003 Agere Systems, March 2003
	AY	Novikov et al.; "Silicon-based Optoelectronics" © 1999-2003 by John Wiley & Sons, Inc.; pp/ 1-6
	AZ	
	BA	

EXAMINER:	DATE CONSIDERED:
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	